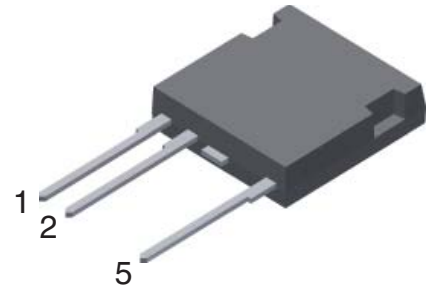
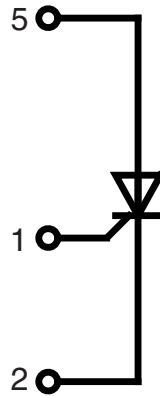


High Voltage Phase Control Thyristor

in High Voltage
ISOPLUS i4-PAC™

$$\begin{aligned} V_{\text{DRM}} = V_{\text{RRM}} &= 2500 \text{ V} \\ I_{\text{T(AV)}} &= 18 \text{ A} \\ I_{\text{TSM}} &= 200 \text{ A} \end{aligned}$$

Part number
CS 20-25mo1F



Features / Advantages:

- high voltage thyristor
 - for line frequency
 - chip technology for long term stability
- ISOPLUS i4-PAC™ high voltage package
 - isolated back surface
 - enlarged creepage towards heatsink
 - enlarged creepage between high voltage pins
 - application friendly pinout
 - high reliability
 - industry standard outline

Applications:

- controlled rectifiers
 - power supplies
 - drives
- AC switches
- capacitor discharge control
 - flash tubes
 - X-ray and laser generators

Package: i4-Pac

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

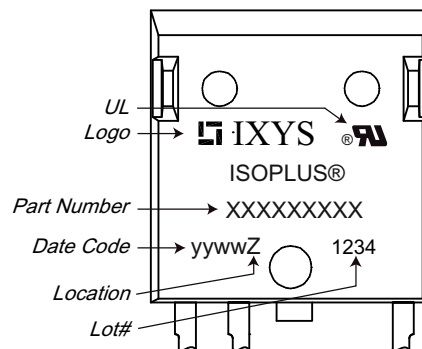
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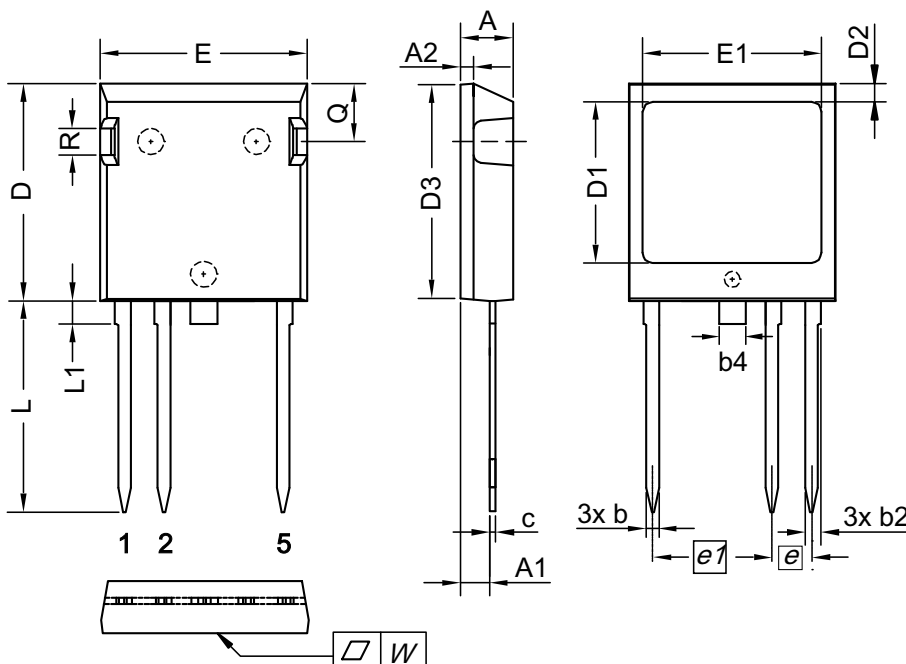
Thyristor			Ratings				
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
$V_{DRM, RRM}$	max. repetitive blocking voltage				2500	V	
$I_{T(AV)}$	average forward current	sine 180° square; $d = 1/3$			18	A	
$I_{T(AV)}$					16	A	
I_{TSM}	max. surge on-state current	sine 180°; $t = 10$ ms; $V_R = 0$ V			200	A	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = T_{VJM}$ $f = 50$ Hz; $t_p = 200$ μ s	repetitive, $I_T = 40$ A			100	A/ μ s
		$V_D = 2/3 V_{DRM}$ $I_G = 0.45$ A $di_G/dt = 0.45$ A/ μ s	non repetitive, $I_T = 20$ A			250	A/ μ s
$(dv/dt)_{cr}$	critical rate of rise of voltage	$T_{VJ} = T_{VJM}$; $V_D = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)			2500	V/ μ s	
V_T	forward voltage	$I_T = 20$ A	$T_{VJ} = 25^\circ\text{C}$		1.3	V	
			$T_{VJ} = 125^\circ\text{C}$		1.3	V	
V_{GT}	gate trigger voltage	$V_D = 6$ V	$T_{VJ} = 25^\circ\text{C}$		2.3	V	
I_{GT}	gate trigger current				250	mA	
V_{GD}	gate non-trigger voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$		0.2	V	
I_{GD}	gate non-trigger current				5	mA	
I_L	latching current	$t_p = 10$ μ s; $V_D = 6$ V $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μ s	$T_{VJ} = 25^\circ\text{C}$		500	mA	
I_H	holding current	$V_D = 6$ V; $R_{GK} = \infty$	$T_{VJ} = 25^\circ\text{C}$		150	mA	
t_{gd}	gate controlled delay time	$V_D = 1/2 V_{DRM}$ $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μ s	$T_{VJ} = 25^\circ\text{C}$		2	μ s	
I_R	reverse current	$V_R = V_{RRM}$; $V_D = V_{DRM}$	$T_{VJ} = 25^\circ\text{C}$		50	μ A	
I_D	drain current		$T_{VJ} = 125^\circ\text{C}$		2	mA	
R_{thJC}	thermal resistance junction to case	DC current			0.92	K/W	
R_{thJH}	thermal resistance case to heatsink	DC current			0.15	K/W	

Package I4-Pac			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				5.5		g
F_c	mounting force with clip		20		120	N
$d_{Spp/App}$ $d_{Spb/Appb}$	creepage distance on surface striking distance through air	terminal to terminal terminal to backside	7.2 5.1			mm mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 2500			V V
			50/60 Hz, RMS, $I_{ISOL} \leq 1$ mA			

Product Marking



Dimensions in mm (1 mm = 0.0394")



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81 BSC		0.150 BSC	
e1	11.43 BSC		0.450 BSC	
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convexbow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side